LOW ENERGY IMPLEMENTATION HYDROGEN FACILITY FOR LABORATORY AND INDUSTRIAL APPLICATIONS

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The need of creation and also requirements to the construction are considered. The principle of action and physical-technical characteristics of low temperature implantation of hydrogen isotopes facility to the semiconductor structures and to the layers of metals to obtain radioisotopes energy sources of milliwatt power and β-, *X*-radiation sources, and neutrons accumulated targets of charged particles based on tritium accelerators are given. The preliminary results on deuterium p-i-n structure implantation of amorphous hydrogenated then dehydrogenation and implanted by heavy hydrogen silicon, which prove the possibility of low temperature implantation of tritium to these structures are given.